Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK982

High Speed Switching Applications Analog Switch Applications Interface Applications

• Excellent switching times: ton = 14 ns (typ.)

 $\bullet~$ High forward transfer admittance: | Y_{fs} | = 100 mS (min)

 $@I_D = 50 \text{ mA}$

• Low on resistance: RDS (ON) = 0.6Ω (typ.) @ ID = 50 mA

• Enhancement-mode

• Complementary to 2SJ148

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DS}	60	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC	I _D	200	mA	
	Pulse	I _{DP}	800		
Drain power dissipation		D-	400	mW	
(Ta = 25°C)		P _D	400		
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

1. SOURCE 2. DRAIN 3. GATE

JEDEC TO-92

JEITA SC-43

TOSHIBA 2-5F1H

Weight: 0.21 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

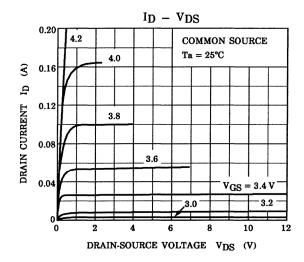


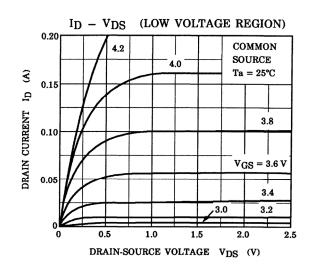
Electrical Characteristics (Ta = 25°C)

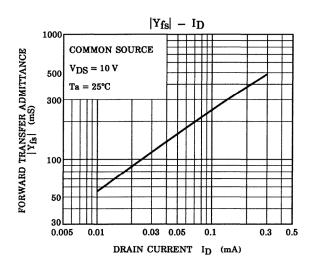
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curr	ent	I _{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	_	_	±100	nA
Drain cut-off current		I _{DSS}	V _{DS} = 60 V, V _{GS} = 0	_	_	10	μА
Drain-source brea	kdown voltage	V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0$	60	_	_	V
Gate threshold vol	Itage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2	_	3.5	V
Forward transfer a	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 50 mA	100	_	_	mS
Drain-source ON r	resistance	R _{DS} (ON)	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$	_	0.6	1.0	Ω
Drain-source ON v	ain-source ON voltage $V_{DS (ON)}$ $I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$		$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$	_	30	50	mV
Input capacitance		C _{iss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz	_	55	65	pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz	_	13	18	pF
Output capacitance		Coss	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	40	50	pF
Switching time	Rise time	t _r	$I_{D} = \underbrace{100 \text{ mA}}_{VOUT}$ $V_{DD} = \underbrace{30 \text{ V}}_{VDD} = \underbrace{30 \text{ V}}_{VDD}$ $V_{IN}; t_{r}, t_{f} < 5 \text{ ns}$ $D.U \le 1\% (Z_{out} = 50 \Omega)$	_	8	_	- ns
	Turn-on time	t _{on}		_	14	_	
	Fall time	t _f		_	35		
	Turn-off Time	t _{off}		_	75	_	

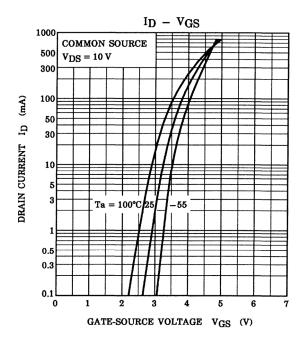
Note: This transistor is the electrostatic sensitive device.

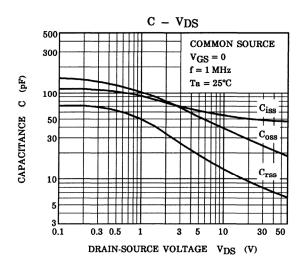
Please handle with caution.



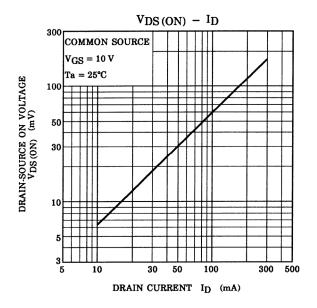


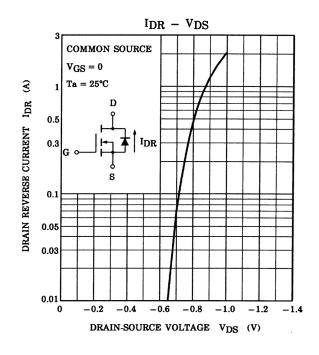


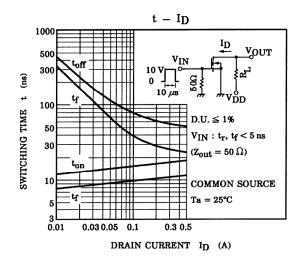


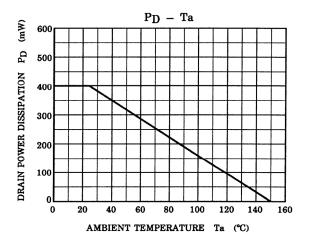


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20070701-EN GENERAL

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